

PTO/SB/08A INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	Not Yet Assigned <i>10/015,102</i>
				Filing Date	Herewith <i>07/08/2003</i>
				First Named Inventor	Henry W. White
Sheet	1	of	3	Attorney Docket No.	UMO 1512.2

U.S. PATENT DOCUMENTS					
Examiner Initials*	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY
		Number	Kind Code ² (if known)		
FH.	1	3,713,822		Kiess	01-30-1973
	2	3,728,784		Schmidt	04-24-1973
	3	3,728,785		Schmidt	04-24-1973
	4	3,801,384		Schmidt	04-02-1974
	5	4,626,322		Switzer	12-02-1986
	6	5,141,564		Chen et al.	08-25-1992
	7	5,274,251		Ota et al.	12-28-1993
	8	5,248,631		Park et al.	09-28-1993
	9	5,574,296		Park et al.	11-12-1996
	10	5,620,557		Manabe et al.	04-15-1997
	11	5,679,965		Schetzina	10-21-1997
	12	5,689,123		Major et al.	11-18-1997
	FH.	13	5,846,844		Akasaki et al.

FOREIGN PATENT DOCUMENTS							
Examiner Initials*	Cite No. ¹	Foreign Patent Document			Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	T ^o
		Office	Number ⁴	Kind Code ² (if known)			

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¹Unique citation designation number. ²See attached Kinds of U.S. Patent Documents. ³Enter Office that issued the document, by the two-letter code (WIPO Standard ST.3). ⁴For Japanese patent documents, the indication of the year of the reign of the Emperor must precede the serial number of the patent document. ⁵Kind of document by the appropriate symbols as indicated on the document under WIPO Standard ST. 16 if possible. ⁶Applicant is to place a check mark here if English language Translation is attached.

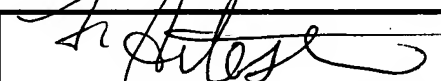
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PCT/IS/08A INFORMATION DISCLOSURE STATEMENT BY APPLICANT (use as many sheets as necessary)				Complete if Known	
				Application Number	Not Yet Assigned ^{10/6/15/102}
				Filing Date	Herewith 7/8/2003
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F.H.	14	EPO	EP 0 863 555	A2	Masashi et al.	09-09-1998	
F.H.	15	PCT	WO 00/08691		White et al.	02-17-2000	

OTHER ART - NON PATENT LITERATURE DOCUMENTS

Examiner Initials*	Cite No. ¹	Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.) date, page(s), volume-issue number(s), publisher, city and/or country where published.					T ⁶
F.H.	16	BAGNALL et al., Optically pumped lasing of ZnO at room temperature, <i>Appl. Phys. Lett.</i> , April 1997, pp. 2230-32, Vol. 70, No. 17					
↑	17	CRACIUN et al., Growth of ZnO thin films on GaAs by pulsed laser deposition, <i>Thin Solid Films</i> , 1995, pp. 1-4					
	18	GUNSHOR et al., Blue-green laser-diode technology moves ahead, <i>Laser Focus World</i> , March 1995, pp. 97-100					
	19	HIRAMATSU et al., Transparent conducting ZnO thin films prepared by XeCl excimer laser ablation, <i>J. Vac. Sci. Technol.</i> , Mar/Apr. 1998, pp. 669-73, Vol. 16, No. 2					
	20	MINEGISHI et al., Growth of p-type Zinc Oxide Films by Chemical Vapor Deposition", <i>J. Appl. Phys.</i> , 1997, pp. 1453-55, Vol. 36, Pt. 2, No. 11A					
	21	JOSEPH et al., p-Type Electrical Conduction in ZnO Thin Films by Ga and N Codoping, <i>Jpn. J. Appl. Phys.</i> , November, 1999, pp. L1205-07, Vol. 38, Part 2, No. 11A, Japanese Journal of Applied Sciences					
	22	MOHAMMAD et al., Reactive Molecular-Beam Epitaxy for Wurzite GaN, <i>MRS Bulletin</i> , Feb. 1997, pp. 22-28					
	23	NAKAMURA, Blue-Green Light Emitting Diodes and Violet Laser Diodes, <i>MRS Bulletin</i> , Feb. 1997, pp. 29-35					
	24	OHTOMO et al., Mg ₂ Zn _{1-x} as a II-VI widegap semiconductor alloy, <i>Appl. Phys. Lett.</i> , May 1998, pp. 2466-68, Vol. 72, No. 19					
✓	25	PEARTON et al., GaN and Related Materials for Device Applications, <i>MRS Bulletin</i> , Feb. 1997, pp. 17-21					
F.H.	26	PONCE, Defects and Interfaces in GaN Epitaxy, <i>MRS Bulletin</i> , Feb. 1997, pp. 51-57					

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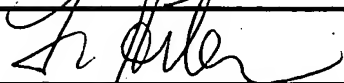
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EVH	27	REYNOLDS et al., Similarities In The Bandedge And Deep-Centre Photoluminescence Mechanisms of ZnO and GaN, <i>Solid State Comm.</i> , 1997, pp. 643-46, Vol. 101, No. 9	
↑	28	SHUR et al., GaN/AlGaIn Heterostructure Devices: Photodetectors and Field-Effect Transistors, <i>MRS Bulletin</i> , Feb. 1997, pp. 44-50	
↓	29	ZOLPER et al., Implantation and Dry Etching of Group-III-Nitride Semiconductors, <i>MRS Bulletin</i> , Feb. 1997, pp. 36-43	
↓	30	International Search Report, PCT/US 99/17486	
FH	31	International Search Report, PCT/US00/41952	

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